



LT1001A

NPN SILICON HIGH FREQUENCY TRANSISTOR

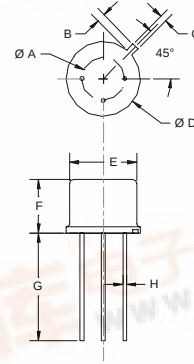
DESCRIPTION:

The **ASILT1001A** is a High Frequency Transistor Designed for High Gain Low Noise CATV, and MATV Amplifier Applications.

MAXIMUM RATINGS

I_C	200 mA
V_{CE}	20 V
P_{DISS}	2.5 W @ $T_C = 50^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+200^\circ\text{C}$
θ_{JC}	70°C/W

PACKAGE STYLE TO-39



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.200 / 5.080	
B	.029 / 0.740	.045 / 1.140
C	.028 / 0.720	.034 / 0.860
D	.335 / 8.510	.370 / 9.370
E	.305 / 7.750	.335 / 8.500
F	.240 / 6.100	.260 / 6.600
G	.500 / 12.700	
H	.016 / 0.407	.020 / 0.508

1 = EMITTER 2 = BASE
3 = COLLECTOR(CASE)

CHARACTERISTICS $T_A = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 5.0\text{ mA}$	20			V
BV_{CBO}	$I_C = 1.0\text{ mA}$	40			V
BV_{EBO}	$I_E = 100\text{ }\mu\text{A}$	3.5			V
I_{CBO}	$V_{CB} = 10\text{ V}$			50	μA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 50\text{ mA}$	70		300	---
$V_{CE(SAT)}$	$I_C = 50\text{ mA}$ $I_B = 5.0\text{ mA}$		500		mV
f_t	$V_{CE} = 14\text{ V}$ $I_C = 90\text{ mA}$ $f = 300\text{ MHz}$		3.0		GHz
C_{cb}	$V_{CB} = 10\text{ V}$ $f = 1.0\text{ MHz}$			1.6	pF
NF	$V_{CE} = 8.0\text{ V}$ $I_C = 50\text{ mA}$ $f = 300\text{ MHz}$		2.5		dB
G_{Umax}	$V_{CE} = 14\text{ V}$ $I_C = 90\text{ mA}$ $f = 300\text{ MHz}$		15		dB